ALPHA & OMEGA SEMICONDUCTOR

# AOUS66416

## 40V N-Channel AlphaSGT™

### General Description

- Trench Power MOSFET - AlphaSGT™ technology
- Low $R_{DS(ON)}$
- Excellent $Q_G$ x $R_{DS(ON)}$ Product (FOM)
- RoHS and Halogen-Free Compliant

### Applications

- High frequency switching and synchronous rectification
- Synchronous rectification MOSFET for Server Power, ATX Power, Adaptor, Telecom power

### Product Summary

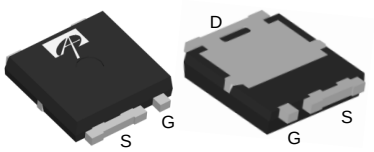
| | |
|---|---|
| $V_{DS}$ | 40V |
| $I_D$ (at $V_{GS}$=10V) | 69A |
| $R_{DS(ON)}$ (at $V_{GS}$=10V) | < 3.3mΩ |
| $R_{DS(ON)}$ (at $V_{GS}$=4.5V) | < 5.0mΩ |

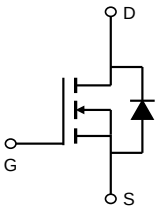
100% UIS Tested
100% Rg Tested

Green Product

**UltraSO-8™**

**Top View** **Bottom View**




| Orderable Part Number | Package Type | Form | Minimum Order Quantity |
|---|---|---|---|
| AOUS66416 | Ultra SO8 | Tape & Reel | 3000 |

**Absolute Maximum Ratings $T_A$=25°C unless otherwise noted**

| Parameter | | Symbol | Maximum | Units |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | 40 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current [G] | $T_C$=25°C | $I_D$ | 69 | A |
| | $T_C$=100°C | | 69 | |
| Pulsed Drain Current [C] | | $I_{DM}$ | 240 | |
| Continuous Drain Current | $T_A$=25°C | $I_{DSM}$ | 33 | A |
| | $T_A$=70°C | | 26.5 | |
| Avalanche Current [C] | | $I_{AS}$ | 30 | A |
| Avalanche energy | L=0.3mH [C] | $E_{AS}$ | 135 | mJ |
| Power Dissipation [B] | $T_C$=25°C | $P_D$ | 73.5 | W |
| | $T_C$=100°C | | 29.5 | |
| Power Dissipation [A] | $T_A$=25°C | $P_{DSM}$ | 6.2 | W |
| | $T_A$=70°C | | 4.0 | |
| Junction and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to 150 | °C |

**Thermal Characteristics**

| Parameter | | Symbol | Typ | Max | Units |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient [A] | t ≤ 10s | $R_{\theta JA}$ | 15 | 20 | °C/W |
| Maximum Junction-to-Ambient [A D] | Steady-State | | 40 | 50 | °C/W |
| Maximum Junction-to-Case | Steady-State | $R_{\theta JC}$ | 1.35 | 1.7 | °C/W |

## Electrical Characteristics ($T_J$=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **STATIC PARAMETERS** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $I_D$=250µA, $V_{GS}$=0V | 40 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$=40V, $V_{GS}$=0V | | | 1 | µA |
| | | $T_J$=55°C | | | 5 | |
| $I_{GSS}$ | Gate-Body leakage current | $V_{DS}$=0V, $V_{GS}$=±20V | | | ±100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$, $I_D$=250µA | 1.4 | 1.95 | 2.5 | V |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}$=10V, $I_D$=20A | | 2.7 | 3.3 | mΩ |
| | | $T_J$=125°C | | 4.2 | 5.1 | |
| | | $V_{GS}$=4.5V, $I_D$=20A | | 3.9 | 5.0 | mΩ |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$=5V, $I_D$=20A | | 100 | | S |
| $V_{SD}$ | Diode Forward Voltage | $I_S$=1A, $V_{GS}$=0V | | 0.7 | 1 | V |
| $I_S$ | Maximum Body-Diode Continuous Current [G] | | | | 69 | A |
| **DYNAMIC PARAMETERS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{GS}$=0V, $V_{DS}$=20V, f=1MHz | | 2575 | | pF |
| $C_{oss}$ | Output Capacitance | | | 440 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 25 | | pF |
| $R_g$ | Gate resistance | f=1MHz | 1 | 2 | 3 | Ω |
| **SWITCHING PARAMETERS** | | | | | | |
| $Q_g$(10V) | Total Gate Charge | $V_{GS}$=10V, $V_{DS}$=20V, $I_D$=20A | | 31 | 50 | nC |
| $Q_g$(4.5V) | Total Gate Charge | | | 13.5 | 24 | nC |
| $Q_{gs}$ | Gate Source Charge | | | 8 | | nC |
| $Q_{gd}$ | Gate Drain Charge | | | 2 | | nC |
| $Q_{oss}$ | Output Charge | $V_{GS}$=0V, $V_{DS}$=20V | | 18 | | nC |
| $t_{D(on)}$ | Turn-On DelayTime | $V_{GS}$=10V, $V_{DS}$=20V, $R_L$=1.0Ω, $R_{GEN}$=3Ω | | 9.5 | | ns |
| $t_r$ | Turn-On Rise Time | | | 3 | | ns |
| $t_{D(off)}$ | Turn-Off DelayTime | | | 33 | | ns |
| $t_f$ | Turn-Off Fall Time | | | 3 | | ns |
| $t_{rr}$ | Body Diode Reverse Recovery Time | $I_F$=20A, di/dt=500A/µs | | 14 | | ns |
| $Q_{rr}$ | Body Diode Reverse Recovery Charge | $I_F$=20A, di/dt=500A/µs | | 30 | | nC |

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A$ =25° C. The Power dissipation $P_{DSM}$ is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation $P_D$ is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A$=25° C.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

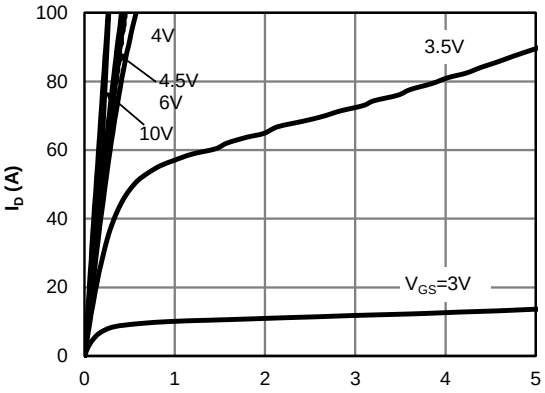



**Figure 1: On-Region Characteristics (Note E)**

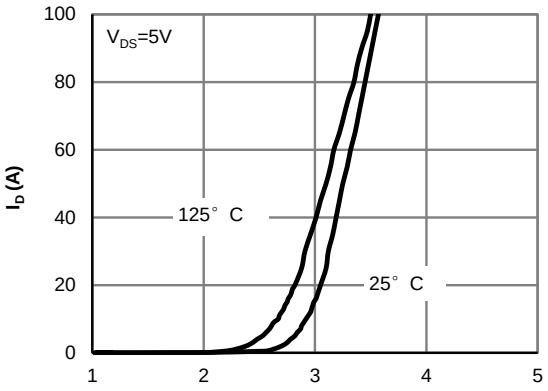



**Figure 2: Transfer Characteristics (Note E)**

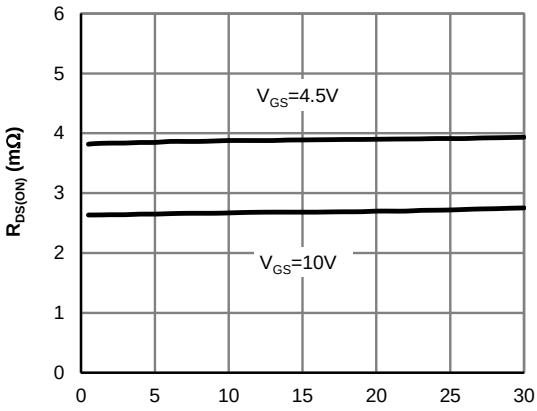



**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**

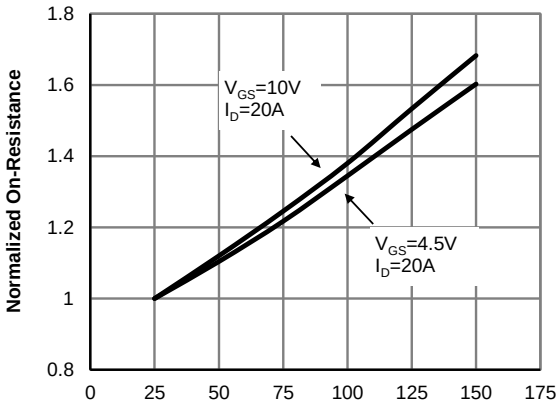



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

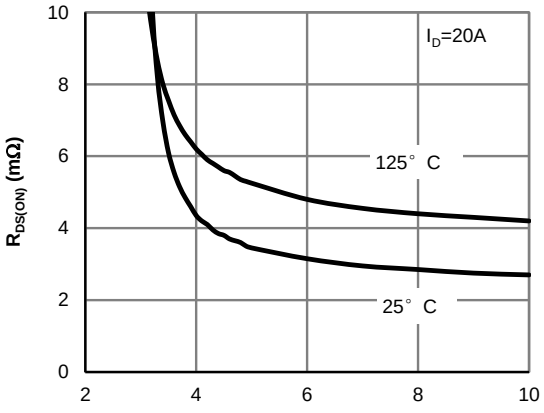



**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

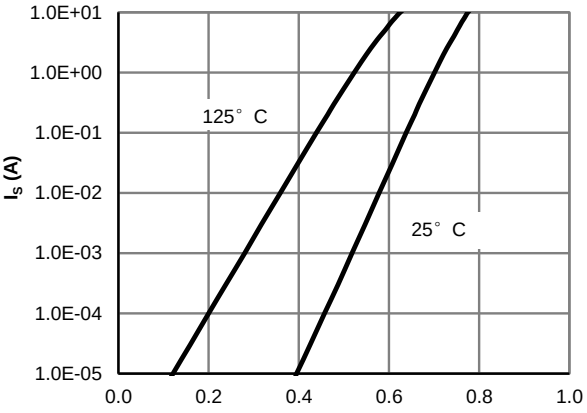



**Figure 6: Body-Diode Characteristics (Note E)**

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

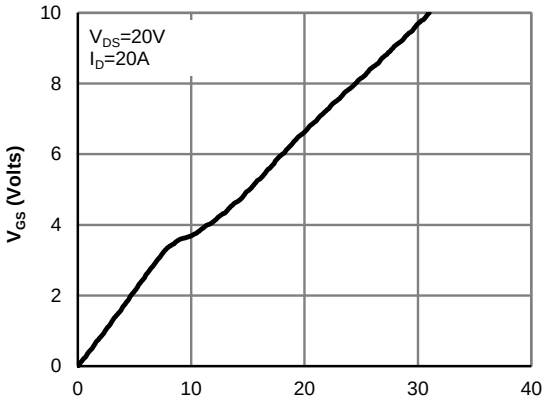



**Figure 7: Gate-Charge Characteristics**

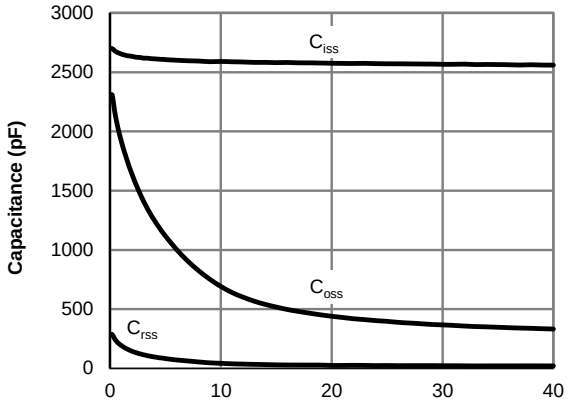



**Figure 8: Capacitance Characteristics**

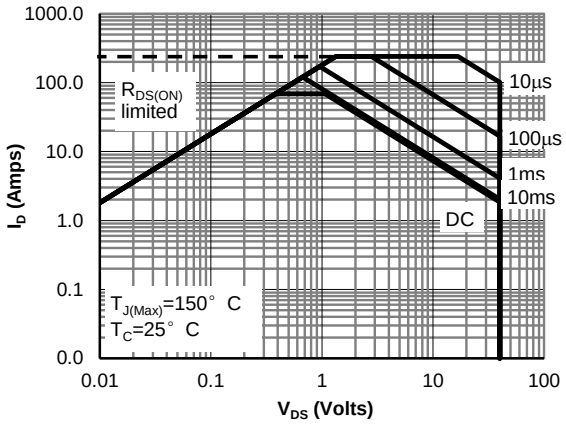



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**

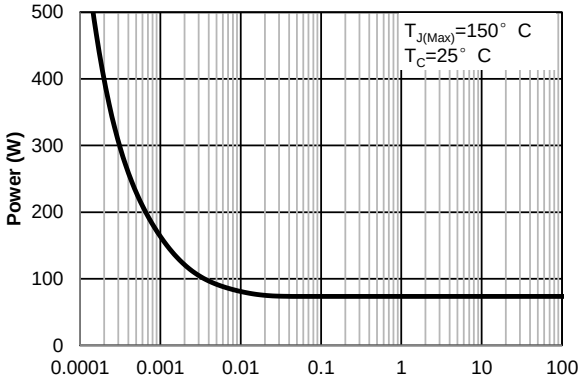



**Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)**

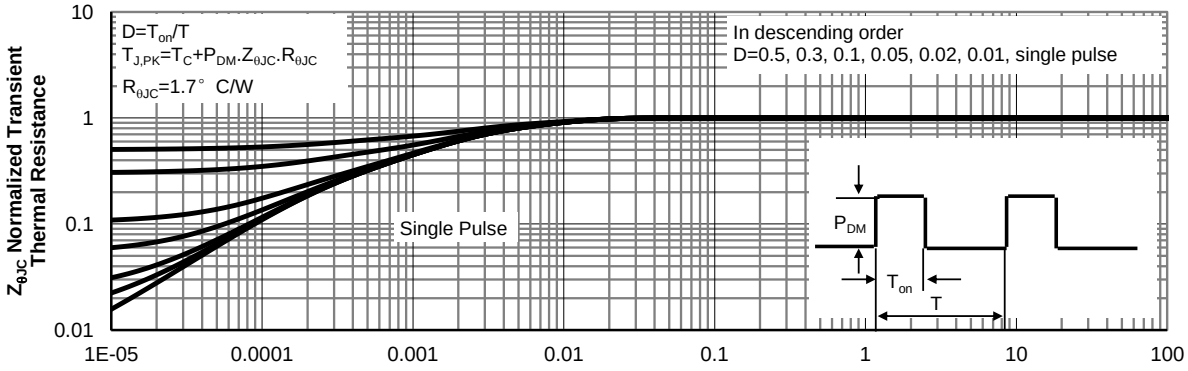



**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

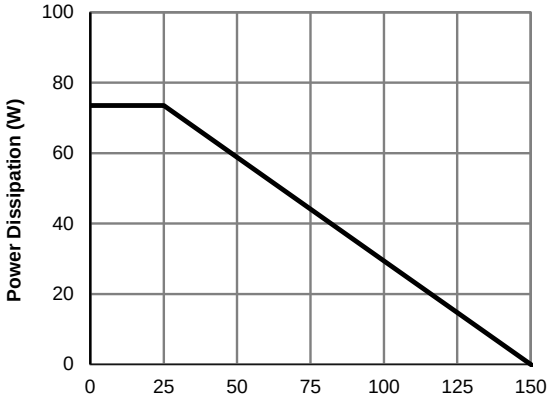



**Figure 12: Power De-rating (Note F)**

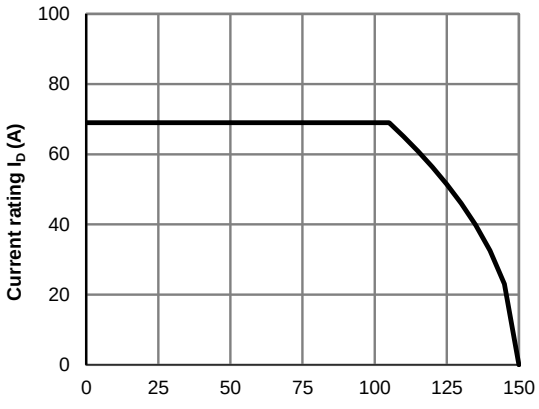



**Figure 13: Current De-rating (Note F)**

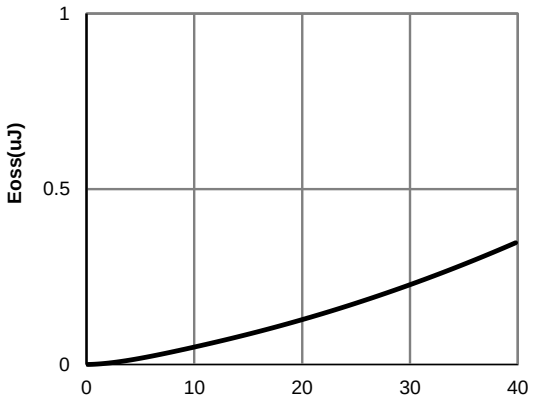



**Figure 14: Coss stored Energy**

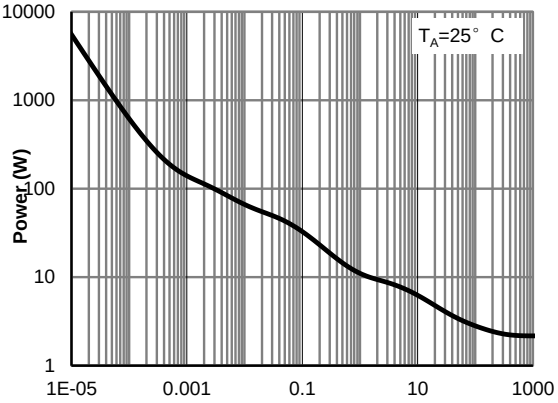



**Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)**

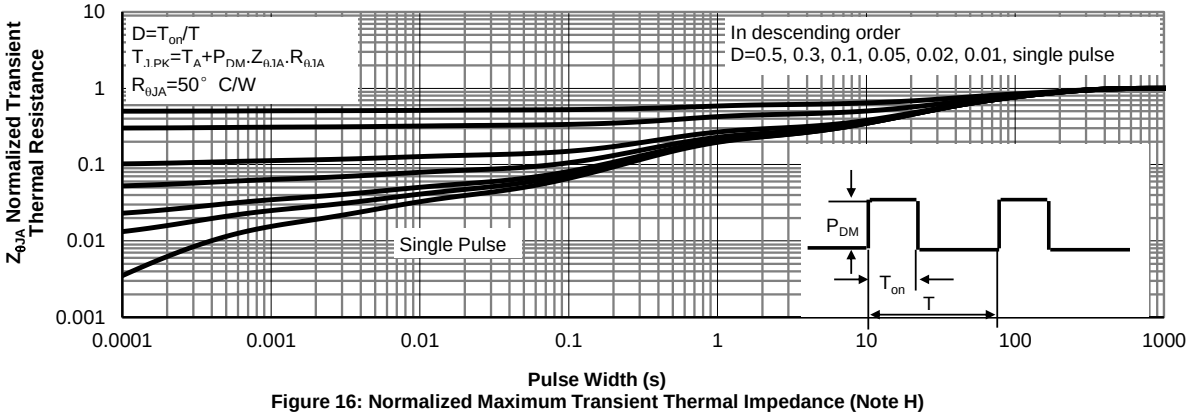



**Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)**

Figure A: Gate Charge Test Circuit & Waveforms

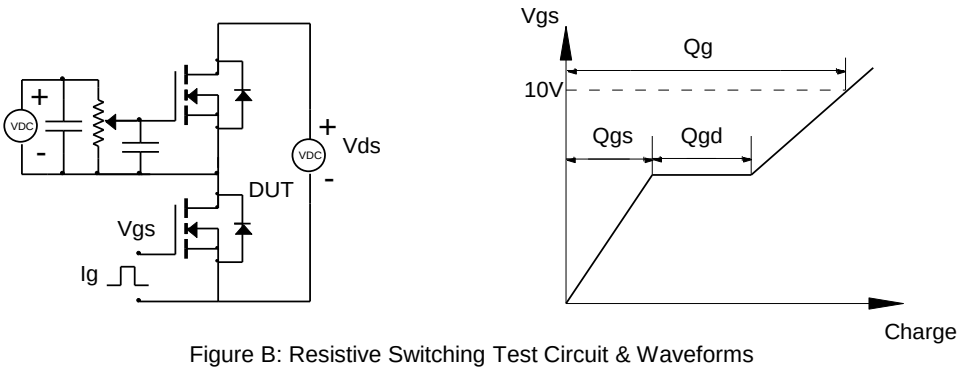



Figure B: Resistive Switching Test Circuit & Waveforms

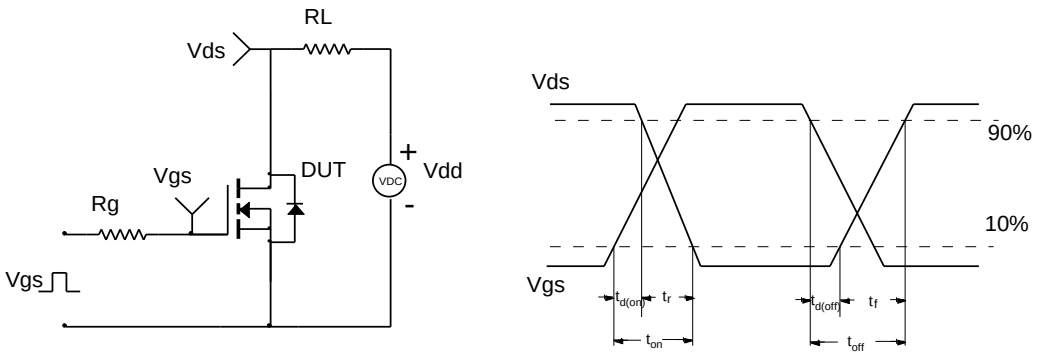



Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

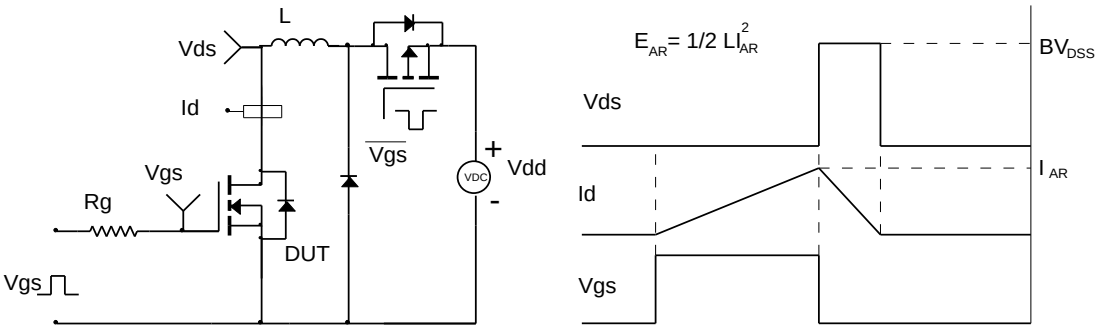



Figure D: Diode Recovery Test Circuit & Waveforms